

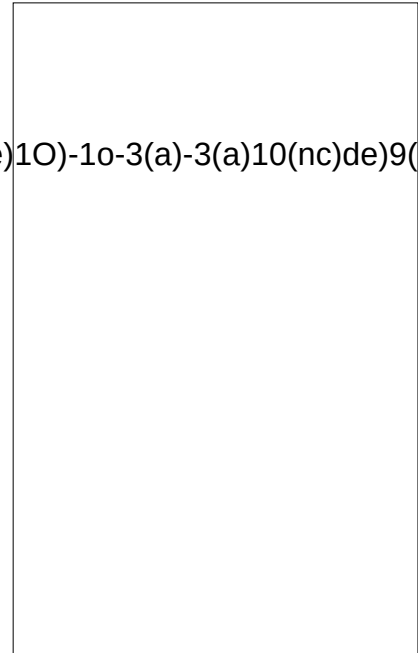


TYN50H-1200SJ 50A SCR

Rev.A.2.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, TYN50H-1200SJ SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is





Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	VW WWW W		

TYN50H-1200SJ

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FIG.1: Maximum power dissipation versus RMS on-state current

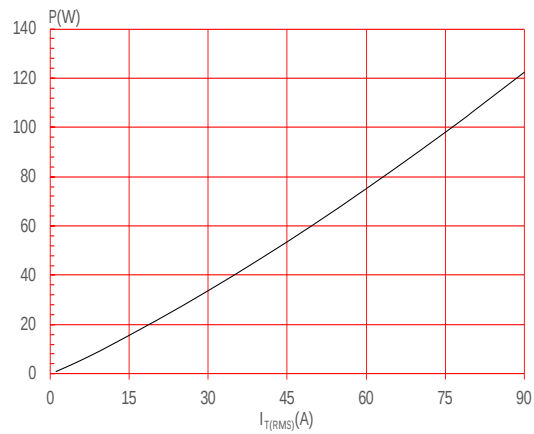


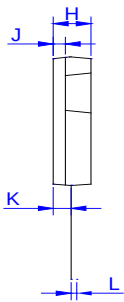
FIG.2: RMS on-state current versus case temperature





FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50		16.10	0.610		0.634
B1	3.10		3.50	0.122		0.138
C						
D	2.90		3.30	0.114		0.130
E	1.90		2.30	0.075		0.091
F	1.00		1.40	0.039		0.055
G						

H	4.80		5.20	0.189		0.205
J						
K						
L						



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